

## SIPMOS<sup>®</sup> Small-Signal-Transistor

### Feature

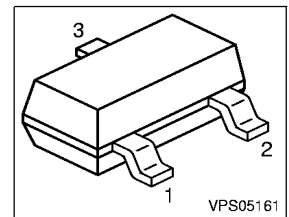
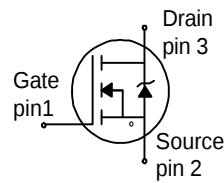
- N-Channel
- Enhancement mode
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant



### Product Summary

|              |     |          |
|--------------|-----|----------|
| $V_{DS}$     | 60  | V        |
| $R_{DS(on)}$ | 5   | $\Omega$ |
| $I_D$        | 0.2 | A        |

### PG-SOT-23



| Type     | Package   | Pb-free | Tape and Reel Information | Marking |
|----------|-----------|---------|---------------------------|---------|
| BSS7728N | PG-SOT-23 | Yes     | L6327: 3000 pcs/reel      | sSK     |

### Maximum Ratings, at $T_j = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

| Parameter                                                                                                                                | Symbol                | Value       | Unit               |
|------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|-------------|--------------------|
| Continuous drain current<br>$T_A=25^{\circ}\text{C}$<br>$T_A=70^{\circ}\text{C}$                                                         | $I_D$                 | 0.2<br>0.16 | A                  |
| Pulsed drain current<br>$T_A=25^{\circ}\text{C}$                                                                                         | $I_{D\text{ puls}}$   | 0.8         |                    |
| Reverse diode dv/dt<br>$I_S=0.2\text{A}$ , $V_{DS}=48\text{V}$ , $di/dt=200\text{A}/\mu\text{s}$ , $T_{j\text{max}}=150^{\circ}\text{C}$ | dv/dt                 | 6           | kV/ $\mu\text{s}$  |
| Gate source voltage                                                                                                                      | $V_{GS}$              | $\pm 20$    | V                  |
| Power dissipation<br>$T_A=25^{\circ}\text{C}$                                                                                            | $P_{\text{tot}}$      | 0.36        | W                  |
| Operating and storage temperature                                                                                                        | $T_j, T_{\text{stg}}$ | -55... +150 | $^{\circ}\text{C}$ |
| IEC climatic category; DIN IEC 68-1                                                                                                      |                       | 55/150/56   |                    |

### Thermal Characteristics

| Parameter                                                      | Symbol     | Values |      |      | Unit |
|----------------------------------------------------------------|------------|--------|------|------|------|
|                                                                |            | min.   | typ. | max. |      |
| Characteristics                                                |            |        |      |      |      |
| Thermal resistance, junction - ambient<br>at minimal footprint | $R_{thJA}$ | -      | -    | 350  | K/W  |

### Electrical Characteristics, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

| Parameter                                                                                                              | Symbol        | Values |        |          | Unit     |
|------------------------------------------------------------------------------------------------------------------------|---------------|--------|--------|----------|----------|
|                                                                                                                        |               | min.   | typ.   | max.     |          |
| Static Characteristics                                                                                                 |               |        |        |          |          |
| Drain-source breakdown voltage<br>$V_{GS}=0, I_D=250\mu A$                                                             | $V_{(BR)DSS}$ | 60     | -      | -        | V        |
| Gate threshold voltage, $V_{GS} = V_{DS}$<br>$I_D=26\mu A$                                                             | $V_{GS(th)}$  | 1.3    | 1.9    | 2.3      |          |
| Zero gate voltage drain current<br>$V_{DS}=60V, V_{GS}=0, T_j=25^{\circ}C$<br>$V_{DS}=60V, V_{GS}=0, T_j=150^{\circ}C$ | $I_{DSS}$     | -<br>- | -<br>- | 0.1<br>5 | $\mu A$  |
| Gate-source leakage current<br>$V_{GS}=20V, V_{DS}=0$                                                                  | $I_{GSS}$     | -      | 1      | 10       |          |
| Drain-source on-state resistance<br>$V_{GS}=4.5V, I_D=0.05A$                                                           | $R_{DS(on)}$  | -      | 4.3    | 7.5      | $\Omega$ |
| Drain-source on-state resistance<br>$V_{GS}=10V, I_D=0.5A$                                                             | $R_{DS(on)}$  | -      | 2.7    | 5        |          |

Electrical Characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### Dynamic Characteristics

|                              |              |                                                                                          |     |     |     |    |
|------------------------------|--------------|------------------------------------------------------------------------------------------|-----|-----|-----|----|
| Transconductance             | $g_{fs}$     | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ ,<br>$I_D = 0.16\text{A}$                  | 0.1 | 0.2 | -   | S  |
| Input capacitance            | $C_{iss}$    | $V_{GS} = 0$ , $V_{DS} = 25\text{V}$ ,<br>$f = 1\text{MHz}$                              | -   | 37  | 56  | pF |
| Output capacitance           | $C_{oss}$    |                                                                                          | -   | 7.3 | 11  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                          | -   | 2.9 | 4.4 |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD} = 30\text{V}$ , $V_{GS} = 10\text{V}$ ,<br>$I_D = 0.2\text{A}$ , $R_G = 6\Omega$ | -   | 2.7 | 4   | ns |
| Rise time                    | $t_r$        |                                                                                          | -   | 2.7 | 4.1 |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                          | -   | 6.1 | 9.1 |    |
| Fall time                    | $t_f$        |                                                                                          | -   | 9   | 13  |    |

### Gate Charge Characteristics

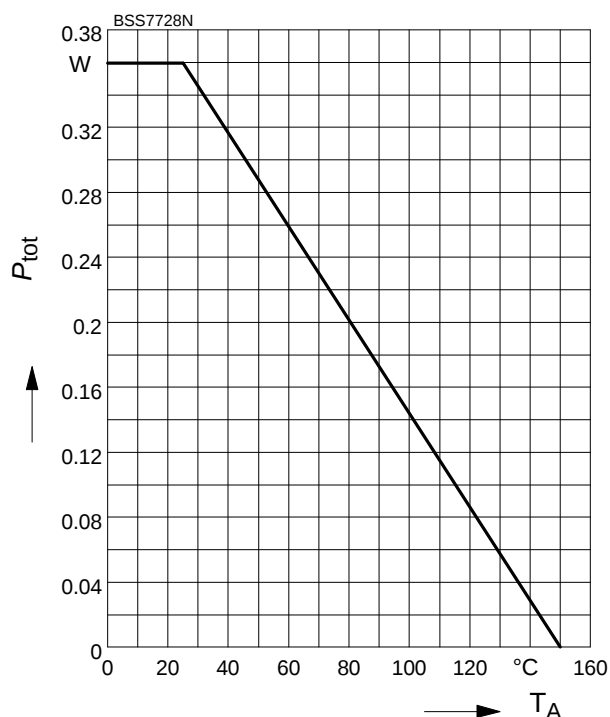
|                       |                 |                                                                               |   |      |      |    |
|-----------------------|-----------------|-------------------------------------------------------------------------------|---|------|------|----|
| Gate to source charge | $Q_{gs}$        | $V_{DD} = 48\text{V}$ , $I_D = 0.2\text{A}$                                   | - | 0.12 | 0.18 | nC |
| Gate to drain charge  | $Q_{gd}$        |                                                                               | - | 0.43 | 0.65 |    |
| Gate charge total     | $Q_g$           | $V_{DD} = 48\text{V}$ , $I_D = 0.2\text{A}$ ,<br>$V_{GS} = 0$ to $10\text{V}$ | - | 1    | 1.5  |    |
| Gate plateau voltage  | $V_{(plateau)}$ | $V_{DD} = 48\text{V}$ , $I_D = 0.2\text{A}$                                   | - | 3.8  | -    | V  |

### Reverse Diode

|                                          |          |                                                                           |   |      |      |    |
|------------------------------------------|----------|---------------------------------------------------------------------------|---|------|------|----|
| Inverse diode continuous forward current | $I_S$    | $T_A = 25^\circ\text{C}$                                                  | - | -    | 0.2  | A  |
| Inv. diode direct current, pulsed        | $I_{SM}$ |                                                                           | - | -    | 0.8  |    |
| Inverse diode forward voltage            | $V_{SD}$ | $V_{GS} = 0$ , $I_F = I_S$                                                | - | 0.84 | 1.2  | V  |
| Reverse recovery time                    | $t_{rr}$ | $V_R = 30\text{V}$ , $I_F = I_S$ ,<br>$di_F/dt = 100\text{A}/\mu\text{s}$ | - | 11.5 | 17.5 | ns |
| Reverse recovery charge                  | $Q_{rr}$ |                                                                           | - | 2.6  | 4    |    |

### 1 Power dissipation

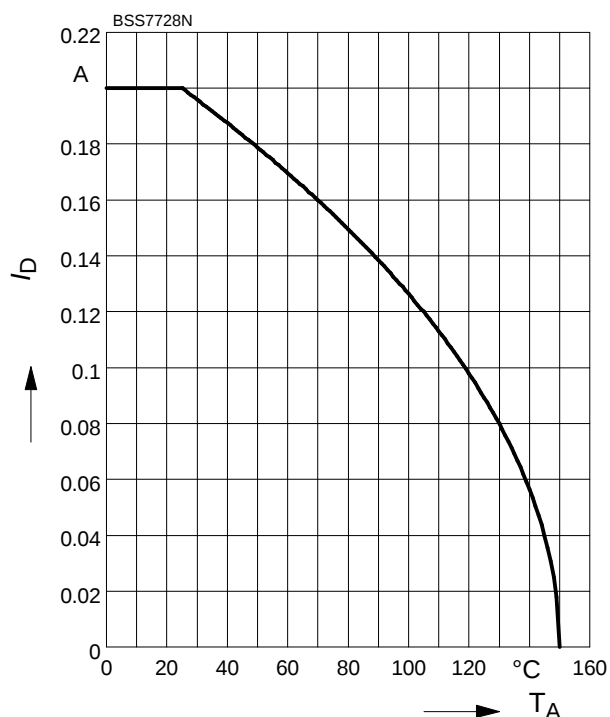
$$P_{\text{tot}} = f(T_A)$$



### 2 Drain current

$$I_D = f(T_A)$$

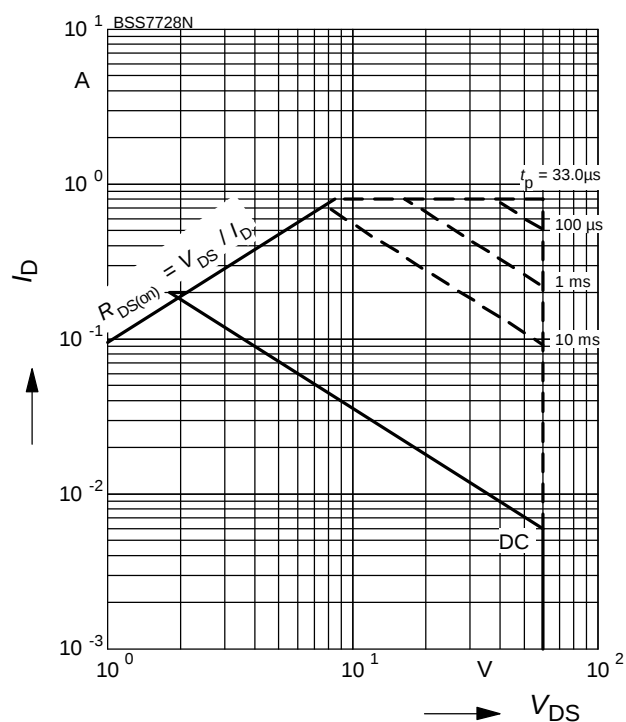
parameter:  $V_{GS} \geq 10$  V



### 3 Safe operating area

$$I_D = f(V_{DS})$$

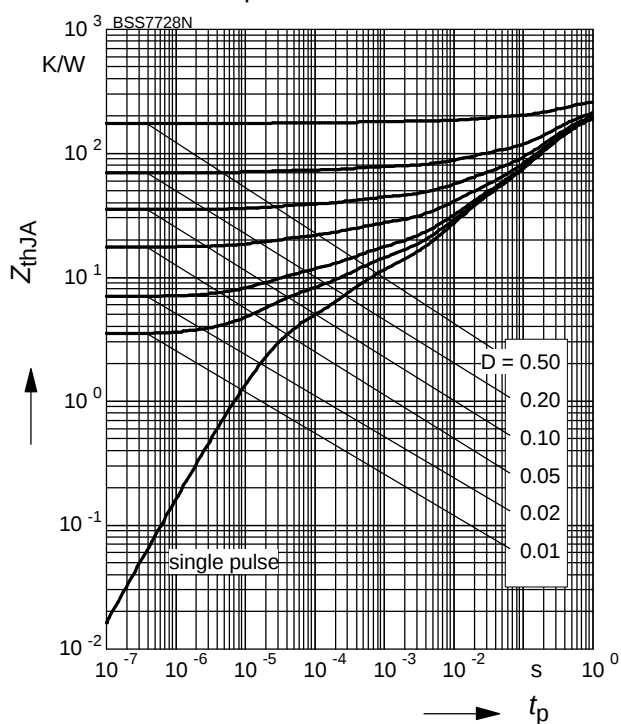
parameter:  $D = 0$ ,  $T_A = 25$  °C



### 4 Transient thermal impedance

$$Z_{thJA} = f(t_p)$$

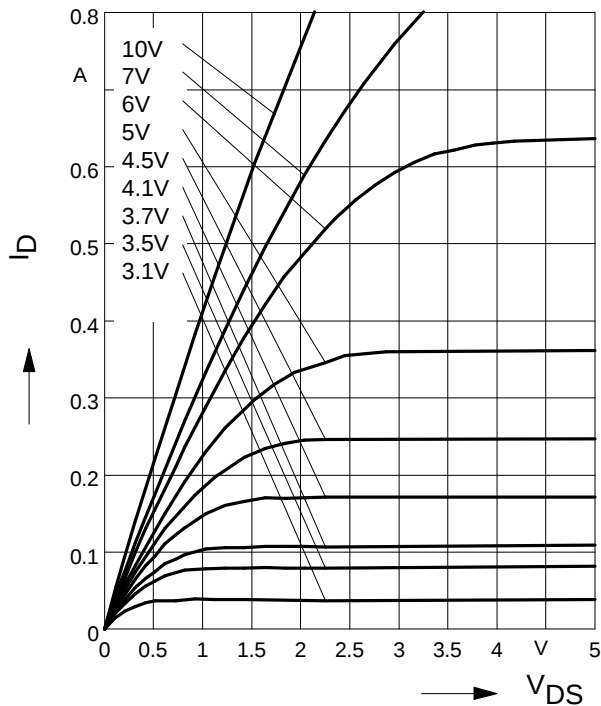
parameter:  $D = t_p / T$



### 5 Typ. output characteristic

$$I_D = f(V_{DS})$$

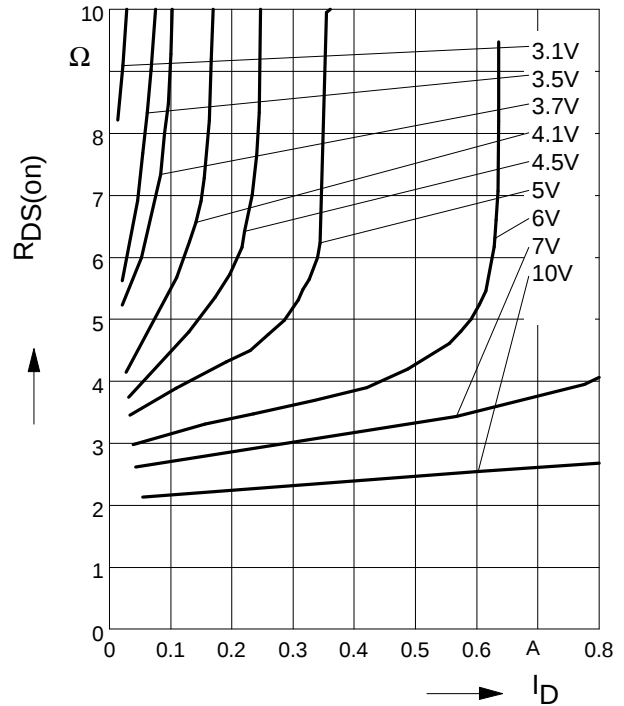
parameter:  $T_j = 25\text{ }^{\circ}\text{C}$ ,  $V_{GS}$



### 6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

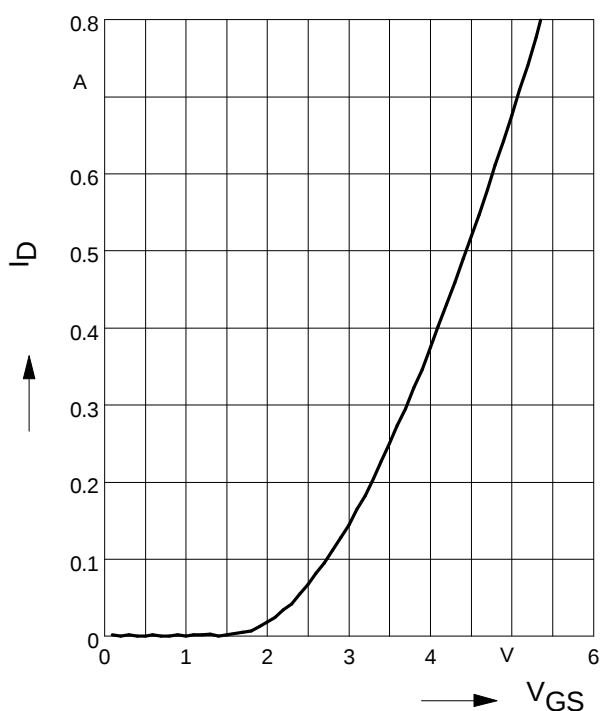
parameter:  $T_j = 25\text{ }^{\circ}\text{C}$ ,  $V_{GS}$



### 7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

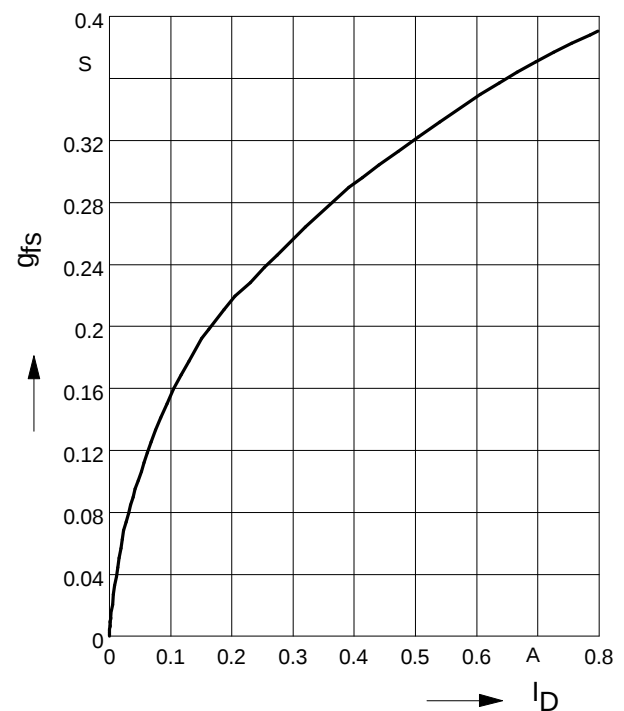
parameter:  $T_j = 25\text{ }^{\circ}\text{C}$



### 8 Typ. forward transconductance

$$g_{fs} = f(I_D)$$

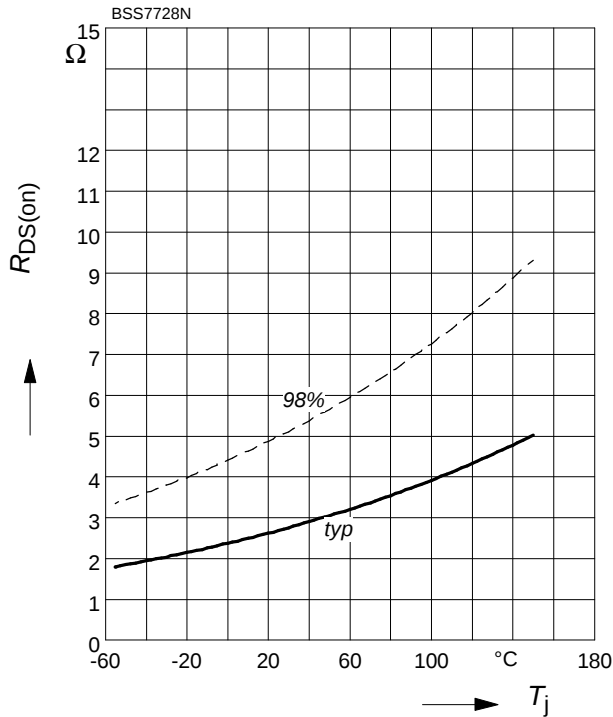
parameter:  $T_j = 25\text{ }^{\circ}\text{C}$



### 9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

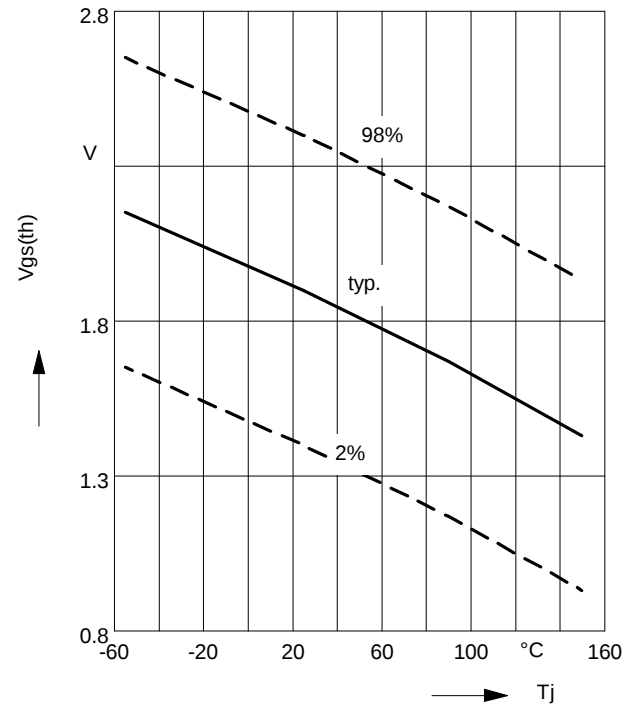
parameter:  $I_D = 0.5 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$



### 10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

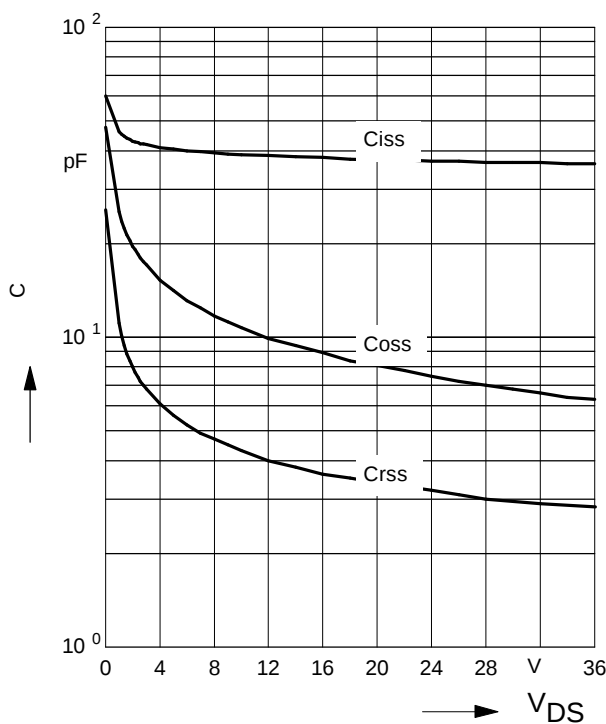
parameter:  $V_{GS} = V_{DS}$ ;  $I_D = 26 \mu\text{A}$



### 11 Typ. capacitances

$$C = f(V_{DS})$$

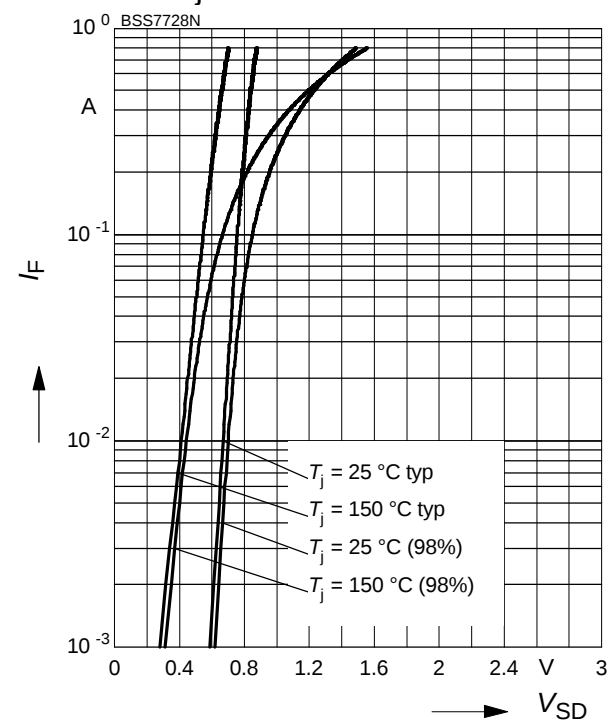
parameter:  $V_{GS} = 0$ ,  $f = 1 \text{ MHz}$ ,  $T_j = 25^{\circ}\text{C}$



### 12 Forward character. of reverse diode

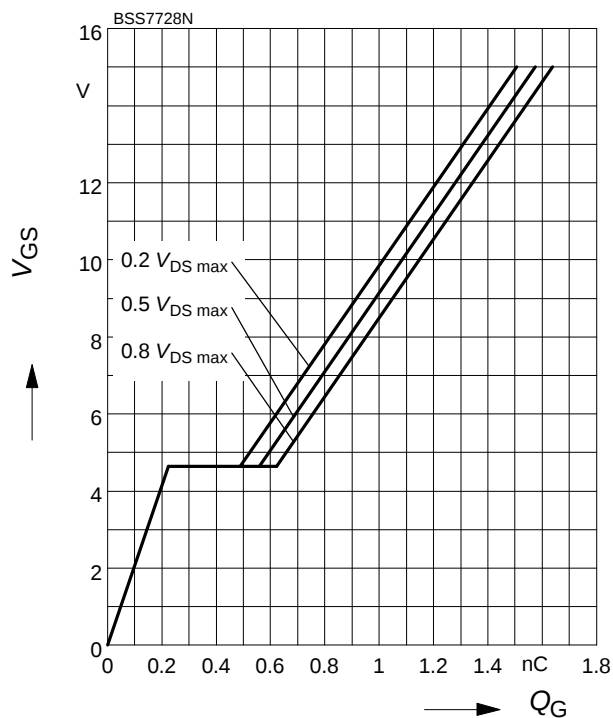
$$I_F = f(V_{SD})$$

parameter:  $T_j$

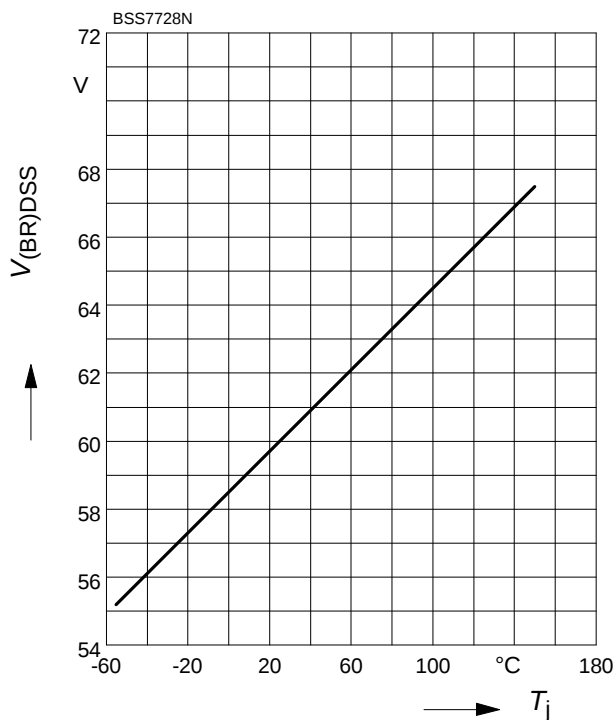


### 13 Typ. gate charge

 $V_{GS} = f(Q_G)$ ; parameter:  $V_{DS}$ ,

 $I_D = 0.5 \text{ A pulsed}, T_j = 25^\circ\text{C}$ 


### 14 Drain-source breakdown voltage

 $V_{(BR)DSS} = f(T_j)$ 


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